NSN 5961-00-905-7619

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Inclosure Material:

Metal all transistor

Overall Length:

0.860 inches all transistor

Overall Diameter:

1.220 inches all transistor

Mounting Facility Quantity:

1 all transistor

Internal Configuration:

Junction contact all transistor

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-67 all transistor

Internal Junction Configuration:

Pnp all transistor

Component Function Relationship:

Matched

Component Name And Quantity:

4 transistor

Mounting Method:

Threaded stud all transistor

Features Provided:

Hermetically sealed case

Thread Size:

0.190 inches all transistor

Semiconductor Material:

Germanium all transistor

Voltage Rating In Volts Per Characteristic:

45.0 breakdown voltage, collector-to-emitter, base open all transistor

Current Rating Per Characteristic:

30.00 amperes source cutoff current all transistor

Power Rating Per Characteristic:

170.0 watts small-signal input power, common-collector absolute all transistor

Transfer Ratio:

45.0 static forward current transfer ratio, common-emitter all transistor and 160.0 static forward current transfer ratio, common-emitter all transistor

Maximum Operating Tempurature Per Measurement Point:

125.0 degrees celsius junction all transistor

Thread Series Designator:

Unf all transistor

Terminal Type And Quantity:

2 tab, solder lug all transistor and 1 threaded stud all transistor

Shelf Life:

N/a

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Demilitarization:

No

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